

### N-channel 30V, 80A, TO-252 Power MOSFET 功率場效應管

#### ■ Features 特點

Low on-resistance and maximum DC current capability 低導通電阻和最大直流電流能力

10V Logic Level Control 邏輯電平控制

$R_{DS(ON)}$  Type 4.7mΩ@VGS=10V

$R_{DS(ON)}$  Type 6mΩ@VGS=5V

#### ■ Applications 應用

Power Management in Note book 筆記本電源管理

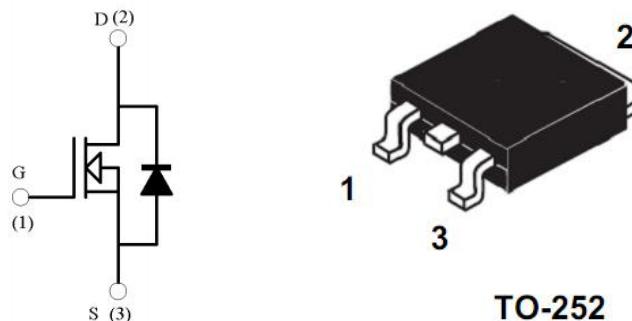
Portable Equipment 便攜式設備

Primary Side Switch 初邊開關

H-bridge Inverter 半橋變換

Car Charger 汽車充電

#### ■ Internal Schematic Diagram 內部結構



#### ■ Absolute Maximum Ratings 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	30	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 20$	V
Drain Current (continuous)漏極電流 - 連續	$I_D$ (at $TC = 25^\circ C$ )	80	A
Drain Current (pulsed)漏極電流 - 脉冲	$I_{DM}$	160	A
Total Device Dissipation 總耗散功率	$P_{TOT}$ (at $TC = 25^\circ C$ )	63	W
Avalanche energy, single pulsed 雪崩能量	EAS	209	mJ
Thermal Resistance Junction to Case 热阻	$R_{\Theta JC}$	2.3	°C/W
Junction/Storage Temperature 結溫/儲存溫度	$T_J, T_{stg}$	-50~175	°C

**■ Electrical Characteristics 電特性**

( $T_A=25^\circ\text{C}$  unless otherwise noted 如無特殊說明，溫度為  $25^\circ\text{C}$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓( $I_D=250\mu\text{A}, V_{GS}=0\text{V}$ )	$\text{BV}_{\text{DSS}}$	30	—	—	V
Gate Threshold Voltage 柵極開启電壓( $I_D=250\mu\text{A}, V_{GS}=V_{DS}$ )	$V_{GS(\text{th})}$	1	1.6	2.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流( $V_{GS}=0\text{V}, V_{DS}=30\text{V}$ )	$I_{\text{DSS}}$	—	—	1	$\mu\text{A}$
Gate Body Leakage 柵極漏電流( $V_{GS}=\pm20\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm100$	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻( $I_D=40\text{A}, V_{GS}=10\text{V}$ ) ( $I_D=30\text{A}, V_{GS}=5\text{V}$ )	$R_{DS(\text{ON})}$	—	4.7 6	6 8	$\text{m}\Omega$
Diode Forward Voltage Drop 內附二極管正向壓降( $I_{SD}=20\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	1.2	V
Input Capacitance 輸入電容 ( $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	1335	—	pF
Common Source Output Capacitance 共源輸出電容( $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	210	—	pF
Reverse Transfer Capacitance 反向傳輸電容 ( $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ )	$C_{RSS}$	—	140	—	pF
Total Gate Charge 總柵極電荷密度 ( $V_{DS}=15\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$ )	$Q_g$	—	5	—	nC
Gate Source Charge 柵源電荷密度 ( $V_{DS}=15\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$ )	$Q_{gs}$	—	3.3	—	nC
Gate Drain Charge 柵漏電荷密度 ( $V_{DS}=15\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$ )	$Q_{gd}$	—	4.8	—	nC
Turn-On Delay Time 開啟延遲時間 ( $V_{DS}=15\text{V}, I_D=15\text{A}, R_{GEN}=3.3\Omega, V_{GS}=10\text{V}$ )	$t_{d(\text{on})}$	—	11	—	ns
Turn-On Rise Time 開啟上升時間 ( $V_{DS}=15\text{V}, I_D=15\text{A}, R_{GEN}=3.3\Omega, V_{GS}=10\text{V}$ )	$t_r$	—	30	—	ns
Turn-Off Delay Time 關斷延遲時間 ( $V_{DS}=15\text{V}, I_D=15\text{A}, R_{GEN}=3.3\Omega, V_{GS}=10\text{V}$ )	$t_{d(\text{off})}$	—	24	—	ns
Turn-On Fall Time 開啟下降時間 ( $V_{DS}=15\text{V}, I_D=15\text{A}, R_{GEN}=3.3\Omega, V_{GS}=10\text{V}$ )	$t_f$	—	6	—	ns

■ TYPICAL CHARACTERISTIC CURVE

典型特性曲線

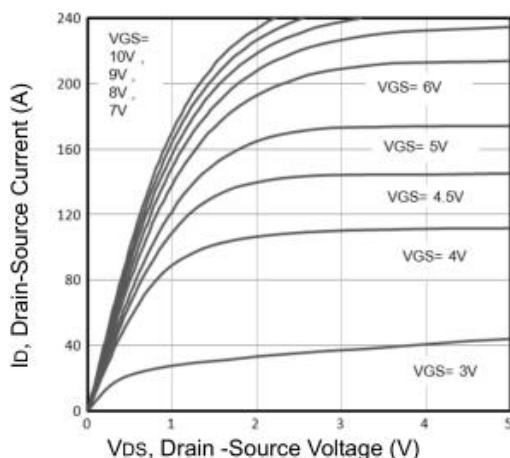


Figure 1: Output Characteristics

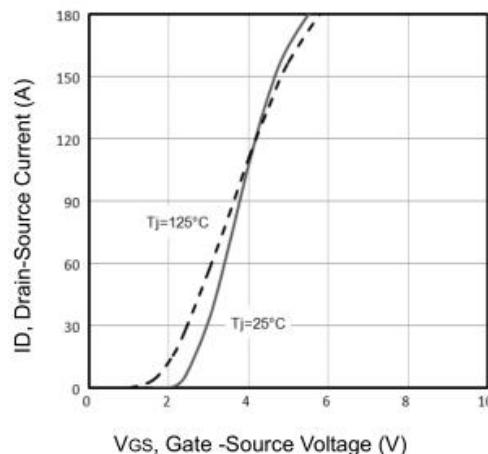


Figure 2: Transfer Characteristics

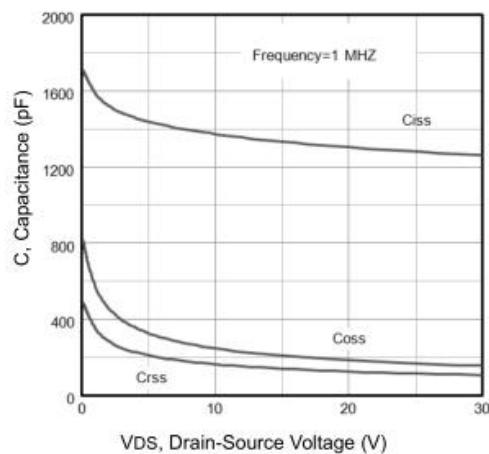


Figure 3: Capacitance

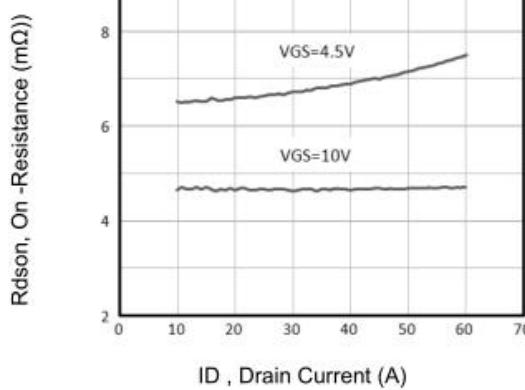


Figure 4:  $R_{dson}$ - Drain Current

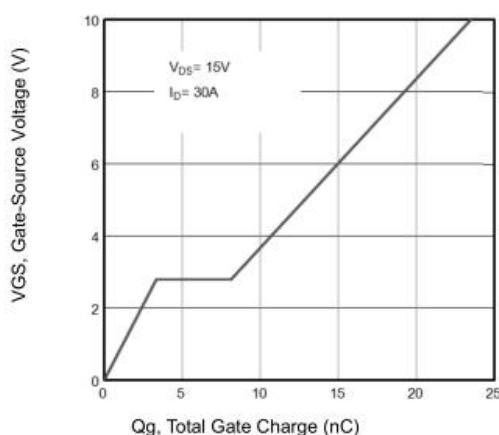


Figure 5: Gate-Charge Characteristics

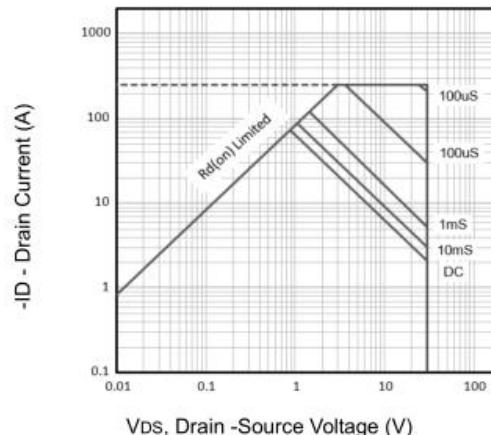
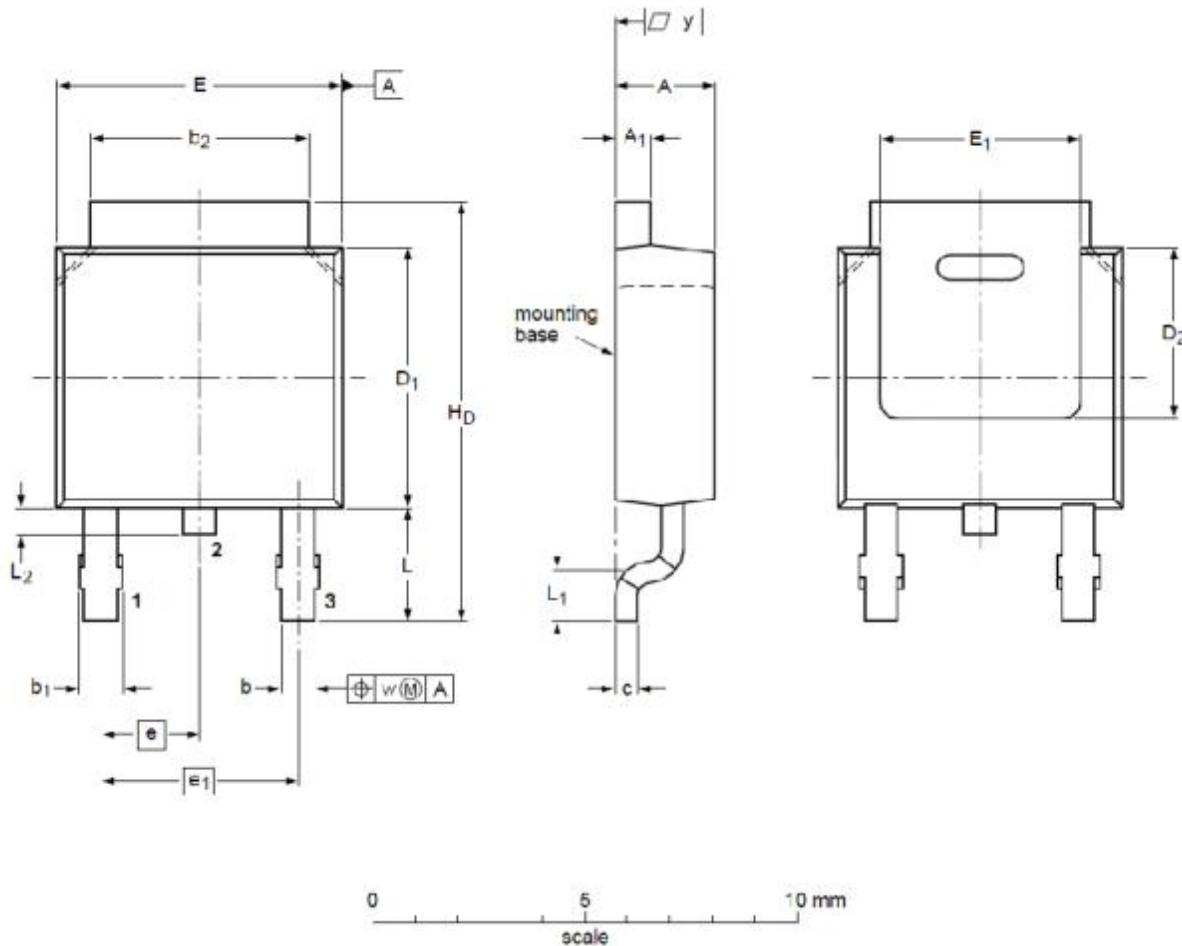


Figure 6: Safe Operating Area

■DIMENSION 外形封裝尺寸



DIMENSIONS ( unit : mm )

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.22	2.30	2.38	A <sub>1</sub>	0.4	0.53	0.65
b	0.68	0.78	0.89	b <sub>1</sub>	0.90	0.98	1.10
b <sub>2</sub>	5.20	5.33	5.55	c	0.45	0.5	0.55
D <sub>1</sub>	5.98	6.10	6.22	D <sub>2</sub>	--	4.00	--
E	6.47	6.60	6.73	E <sub>1</sub>	5.10	5.28	5.45
e	--	2.28	--	e <sub>1</sub>	--	4.57	--
H <sub>0</sub>	9.60	10.08	10.40	L	2.75	2.95	3.05
L <sub>1</sub>	--	0.50	--	L <sub>2</sub>	0.50	--	1.10
w	--	0.20	--	y	0.20	--	--